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	ı			
,				

L Number	Hits	Search Text	DB	Time stamp
-	5	(("5838041") or ("5969383")).PN.	USPAT;	2004/07/30 12:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	4004	(IBM_TDB	2004/07/20 40:05
- :	1604	(nonvolat\$4 adj2 memory) with (first adj2 second)	USPAT;	2004/07/30 12:05
		· ·	US-PGPUB; EPO; JPO;	
1	*		DERWENT;	
			IBM TDB	
<u> </u>	/ 16	(((nonvolat\$4 adj2 memory) with (first adj2 second) with (field	USPAT;	2004/07/30 12:08
	,,,	adj effect adj transistor)) and (gate adj electrode)) and (first	US-PGPUB;	200 1101100 12:00
		near3 region)	EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	6	((((nonvolat\$4 adj2 memory) with (first adj2 second) with	USPAT;	2004/07/30 12:10
		(field adj effect adj transistor)) and (gate adj electrode)) and	US-PGPUB:	
		(first near3 region)) and (second near3 gate adj electrode)	EPO; JPO;	
i l			DERWENT;	
			IBM_TDB	
-	36	(nonvolat\$4 adj2 memory) with (first adj2 second) with (field	USPAT;	2004/07/30 12:12
		adj effect adj transistor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	26	(/nanyalath4 adi2 maman) with (first adi2 accord) with (field	IBM_TDB	2004/09/02 44:46
-	20	((nonvolat\$4 adj2 memory) with (first adj2 second) with (field adj effect adj transistor)) and (gate adj electrode)	USPAT; US-PGPUB;	2004/08/03 11:46
		adj enect adj transistor)) and (gate adj electrode)	EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	
<u> </u>	36942	nonvolat\$4 adj2 memory	USPAT;	2004/08/03 13:20
	000 12	Honvoidte i daje momory	US-PGPUB;	200 1700/00 10:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	569	(nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 12:55
		electrode) same (second near2 gate near2 electrode))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	446	(//www.lat04_d/20	IBM_TDB	
-	419	, , , ,,	USPAT;	2004/08/03 12:54
		electrode) same (second near2 gate near2 electrode))) and	US-PGPUB;	
		((first or second) near4 region)	EPO; JPO;	
			DERWENT; IBM_TDB	
1_ 1	52	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 12:34
	52	electrode) same (second near2 gate near2 electrode))) and	US-PGPUB;	2007/00/00 12.04
		((first or second) near4 region near4 (p adj type))	EPO; JPO;	
		(F ==) (F==)	DERWENT;	
			IBM_TDB	
-	2	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 13:14
]		electrode) same (second near2 gate near2 electrode))) and	US-PGPUB;	
		((first or second) near4 region near4 (first adj type))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	371	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 12:56
		electrode) same (second near2 gate near2 electrode))) and	US-PGPUB;	
ļ		((first or second) near2 region)	EPO; JPO;	İ
			DERWENT;	
			IBM_TDB	

	515	(nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 12:55
•		electrode) with (second near2 gate near2 electrode))	US-PGPUB;	200 1100100 12:00
	Closure and the state of the	EPO; JPO;		
		DERWENT;		
	i		IBM_TDB .	
_	515	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 12:55
		electrode) with (second near2 gate near2 electrode))) and	US-PGPUB;	
		((first near2 gate near2 electrode) with (second near2 gate	EPO; JPO;	
		near2 electrode))	DERWENT;	
			IBM_TDB	
_	344	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 13:08
		electrode) with (second near2 gate near2 electrode))) and	US-PGPUB;	
		((first or second) near2 region)	EPO; JPO;	
		((mat or occord) rights region)	DERWENT;	
			IBM_TDB	
_	344	(((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 13:09
		electrode) with (second near2 gate near2 electrode))) and	US-PGPUB:	200 ,,000,000 ,0.00
		((first or second) near2 region)) and ((first or second) field adj	EPO; JPO;	
		effect)	DERWENT;	1
		,,	IBM_TDB	
_	2	((((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT:	2004/08/03 13:18
	_	electrode) with (second near2 gate near2 electrode))) and	US-PGPUB;	200 1/00/00 10:10
		((first or second) near2 region)) and ((first or second) field adj	EPO; JPO;	
		effect)) and ((first or second) near4 region near4 ((first or	DERWENT:	
		second) adj type))	IBM_TDB	
_	0	((nonvolat\$4 adj2 memory) and ((first near2 gate near2	USPAT;	2004/08/03 13:19
		electrode) with (second near2 gate near2 electrode))) and	US-PGPUB;	200 1/00/00 10:10
		(((first or second) adj region) near4 ((first or second) adj	EPO; JPO;	
		type))	DERWENT:	
			IBM TDB	
_	1037	(nonvolat\$4 adj2 memory) and (charge adj storage)	USPAT;	2004/08/03 14:20
		(US-PGPUB	
	ļ		EPO; JPO;	
			DERWENT	
			IBM_TDB	
_	1037	(nonvolat\$4 adj2 memory) and (charge adj storage)	USPAT:	2004/08/03 14:20
		(US-PGPUB	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1037	(nonvolat\$4 adj2 memory) and (charge adj storage)	USPAT;	2004/08/03 14:49
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	257/257,316,319,321,324,326,315,311,322,326.ccls. and	USPAT;	2004/08/03 14:53
		438/258,592,182,257-267,736,738,592 and ((first or second)	US-PGPUB;	
		adj gate adj electrode)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	(257/257,316,319,321,324,326,315,311,322,326.ccls. and	USPAT;	2004/08/03 14:56
		438/258,592,182,257-267,736,738,592.ccls. and ((first or	US-PGPUB	
		second) adj gate adj electrode)) and 365/185.01,185.18.ccls.	EPO; JPO;	
		, , , , , , , , , , , , , , , , , , , ,	DERWENT;	
			IBM_TDB	
-	46	257/257,316,319,321,324,326,315,311,322,326.ccls. and	USPAT;	2004/08/03 15:26
		438/258,592,182,257-267,736,738,592.ccls. and ((first or	US-PGPUB;	
		second) adj gate adj electrode)	EPO; JPO;	
	1	·	DERWENT;	
	1		IBM_TDB	
-	8	(257/257,316,319,321,324,326,315,311,322,326.ccls. and	USPĀT;	2004/08/03 15:28
		438/258,592,182,257-267,736,738,592.ccls. and ((first or	US-PGPUB;	
		second) adj gate adj electrode)) and (charge adj storage)	EPO; JPO;	
	1		DERWENT:	

US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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